## Ting Liang

## List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/1831509/publications.pdf

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	1684188	1872680	
61	5	6	
citations	h-index	g-index	
8	8	90	
docs citations	times ranked	citing authors	
	citations 8	61 5 citations h-index  8 8	

#	Article	IF	CITATIONS
1	Homo-Junction Bottom-Gate Amorphous In–Ga–Zn–O TFTs With Metal-Induced Source/Drain Regions. IEEE Journal of the Electron Devices Society, 2019, 7, 52-56.	2.1	9
2	Nonlinear photocurrent-intensity behavior of amorphous InZnO thin film transistors. Applied Physics Letters, 2018, 112, .	3.3	8
3	Pâ€1.14: The Influence of Dualâ€channel on the Performance of Selfâ€Align Topâ€Gate IGZO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2018, 49, 561-564.	0.3	0
4	Scalability and Stability Enhancement in Self-Aligned Top-Gate Indium- Zinc-Oxide TFTs With Al Reacted Source/Drain. IEEE Journal of the Electron Devices Society, 2018, 6, 680-684.	2.1	9
5	Oxide Thin-Film Transistors With IMO and IGZO Stacked Active Layers for UV Detection. IEEE Journal of the Electron Devices Society, 2017, 5, 504-508.	2.1	22
6	Pâ€20: Effects of N <sub>2</sub> O Plasma Treatment Time on the Performance of Selfâ€Aligned Topâ€Gate amorphous oxide Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2017, 48, 1299-1302.	0.3	11
7	Pâ€21: The Effect of Thermal Annealing Sequence on the Performance of Selfâ€Aligned Topâ€Gate aâ€IGZO TFTs. Digest of Technical Papers SID International Symposium, 2017, 48, 1303-1306.	0.3	1
8	High reliability of IGZO TFTs using low-temperature fabricated organic passivation layers., 2016,,.		1